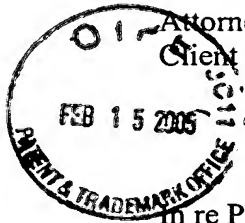Attorney Docket: 040258-0307828
Client Reference: EL01006CDC-D7

FEB 15 2005

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT APPLICATION of: OHMI ET AL.

Confirmation Number: 5332

Application No.: 10/762,520

Group Art Unit: 2818

Filed: January 23, 2004

Examiner: David Vu

Title: FLASH MEMORY DEVICE AND A FABRICATION PROCESS THEREOF, METHOD OF FORMING A DIELECTRIC FILM

REQUEST FOR COMPLETELY INITIALED
PTO-1449 DATED JANUARY 23, 2004

U.S. Patent and Trademark Office
Customer Window – Mail Stop Issue Fee
Randolph Building
401 Dulany Street
Alexandria, VA 22314

Sir:

In reviewing the Notice of Allowance, dated January 27, 2005, Applicants noted that only one page of the three page PTO-1449s that were filed with the application on January 23, 2004 were initialed and returned by the Examiner. The three IDS pages listed all of the prior art filed by the Applicants and cited by the Examiner in the parent application, Serial No. 10/359,701, filed February 7, 2003, which is now allowed.
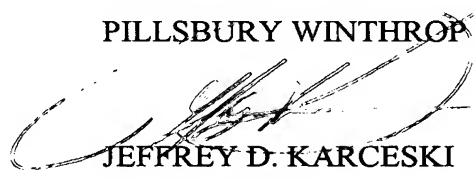
The present application was allowed on the first Office Action, and copies of all of the other 1449s filed in this application and initialed by the Examiner were enclosed with the Notice of Allowance. However, pages 2 and 3 of the PTO-1449s filed with the application were missing. Applicants enclose copies of the second and third PTO-1449 pages for the Examiner's convenience.

It is respectfully requested that the Examiner initial page 2, containing 2 foreign references, and page 3, containing three non-patent literature references, and return both initialed PTO-1449s by facsimile as soon as possible.

Respectfully submitted,

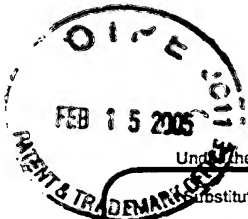PILLSBURY WINTHROP LLP

JEFFREY D. KARCESKI
Reg. No. 35914
Tel. No. 703.905.2110
Customer No. 00909

Date: February 15, 2005

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McLean, VA 22102
(703) 905-2000

2

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Complete if Known	
Application Number	
Filing Date	01/23/2004
First Named Inventor	TADAHIRO OHMI
Art Unit	2818
Examiner Name	
Attorney Docket Number	040258-0307828

Sheet	1	of	

U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code[2] *(if known)*				
		US-				
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FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T[6]
		Country Code[3] Number[4] Kind Code[5] *(if known)*					
	F	JP	9-223752	08-00-1997	MINE		
	G	JP	PCT/JP01/01967	03-00-2001			

Examiner Signature		Date Considered	

FEB 1 5 2005

Substitute for form 1449B/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

	Complete if Known
Application Number	
Filing Date	01/23/2004
First Named Inventor	TADAHIRO OHMI
Art Unit	2818
Examiner Name	

Sheet		1	of	1	Attorney Docket Number	040258-0307828

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
	1	ITO ET AL., "Silicon Oxynitridation WIth Inductively Coupled Oxygen-Nitrogen Mixed Plasma," Jpn. J. Appl. Phys., p. 612-616, (1997).	
	2	HIRAYAMA ET AL., "Low Temperature Growth of High-Integrity Silicon Oxide Films by Oxygen Radical Generated in High-Density Krypton-Plasma," IEEE, p. 249-252, (1999).	
	3	SAITO ET AL., "Low Temperature Formation of Gate-Grade Silicon Nitride Film Employing Microwave-Excitation High-Density Plasma," Technical Report, IEICE, p. 85-90, (1999).	

Examiner Signature		Date Considered	